## UNIT: 2 AMPLIFIERS AT HIGH TREQUENCES

Low frequency analytisis:

- a) All entrenal rapacitances (Ce, Cb, Cc) Show their effect in son frequency region tence they cannot be neglected.
- b) ell internal capacitances behave as open Circuit in low frequency regions. Hence they need not be considered.
- c) the approximation BIT should be replaced with its approx. L-parameter model during analysis. (For FET dow frequency model)

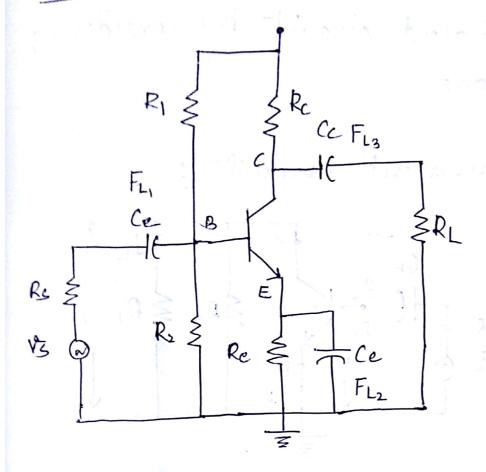
Mid frequency analysis:

- a) All entirnal capacitances behave as short circuit.
- b) du junction capacitances behave as open Circuit.
- c) BIT is to be replaced with approx. h-parameter model.

High frequency analysis:

All enternal capacitations behave as short circuit. b) All Junction capacitances show their effect un high frequency region, hence cannot be neglected. e) BIT should be replaced with hybrid To BIT should be replaced with hybrid To model during analysis. (For FET, high trequency model)

LOW FREQUENCY ANALYSIS:



3. les approx. h-parameter model for BJT.

4. When the is considered, short circuit to & Cc.

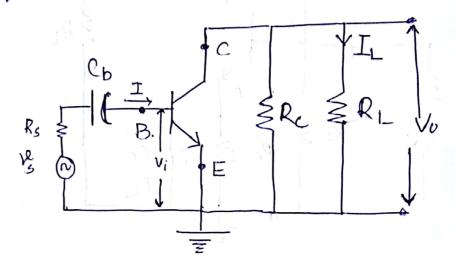
" Ce " " Cb & Cc

" Cc " " " Ce & Cb

Analysis :

Ac equivalent circuit by considering Cp alone.

## Ac requiralent circuit:



## h-parameter model:

$$V_{s} \stackrel{R_{s}}{\bigcirc} \stackrel{C_{b}}{\longrightarrow} \stackrel{I}{\longrightarrow} \stackrel{I}{\longrightarrow} \stackrel{R_{e}}{\longrightarrow} \stackrel{R_{e$$

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$$V_{0} = \frac{-hfeV_{S}RL'}{Z}$$

$$AV = \frac{-hfeV_{S}RL'}{Z}$$

$$Z = (hie + R_{S}) + \frac{1}{fWC_{b}}$$

$$= (R_{S} + hie) \left[ 1 + \frac{1}{j2\pi fc_{S}(R_{S} + hie)} \right]$$

$$= (R_{S} + hie) \left[ 1 - \frac{1}{jfL_{1}} \right]$$

$$where, f_{L_{1}} = \frac{1}{2\pi (R_{S} + hie)(b)}$$

$$= \lambda AV = \frac{-hfeRL'}{(R_{S} + hie)(1 - \frac{1}{jfL_{1}})}$$

$$AV = \frac{Amax}{Amax}$$

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$$AV = \frac{Amax}{Amax}$$

$$Av = \frac{Amax}{(1-jf_{li})}$$
where  $Amax = \frac{-heR_{l}}{Rs + hie}$ 

